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Data Sheet No. PD-3.083

INTERNATIONAL RECTIFIER



T- 25-17

2N3091 SERIES

110 Amp RMS SCRs

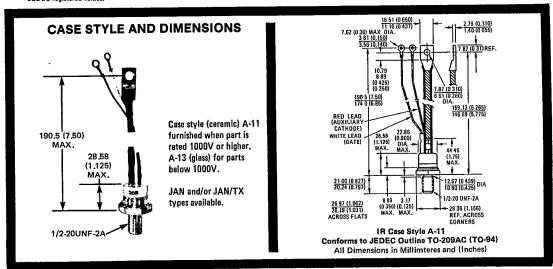
Major Ratings and Characteristics

		2N3091-98	Units		
I _{T(RMS)}		110	Α		
I _{T(AV)}		70*	Α		
⊕ Max. T _C		62*	°C		
ITSM	-@ 50 Hz	955	_		
	@ 60 Hz	1000*	Α		
l ² t	@ 50 Hz	4550	A ² s		
	@ 60 Hz	4150	A-5		
I _{GT}		110	mA		
dv/dt 1		20*	V/μs		
di/dt		300	A/μs		
Tj		40 to 125	°C		
V _{RRM} , V _{DRM} range		600 to 1300	V		

Description/Features

- Bulk Avalanche
- Can be supplied as JAN devices in accordance with MIL-S-19500/280A
- Forward and reverse ratings from 600 - 1300 volts.

*JEDEC registered values.



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2N3091 Series

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VOLTAGE RATINGS (Applied gate voltage zero or negative)

Part Number ①	V _{RRM} — V _{DRM} Max. Repetitive Peak Reverse and Off-State Voltage (V) ②	V(BR)R Min. Reverse Avalanche Voltage
	$T_{J} = -40^{\circ} \text{C to } 125^{\circ} \text{C}$	T _J = 25°C
2N3091 2N3092 2N3093 2N3094 2N3095 2N3096 2N3097 2N3098	600* 700* 800* 900* 1000* 1100* 1200* 1300*	700* 800* 900* 1000* 1100* 1200* 1300* 1400*

ELECTRICAL SPECIFICATIONS

		2N3091-98	Units	Conditions	
	ON-STATE				
I _T (RMS)	Max. RMS on-state current	110	A		
I _{T(AV)}	Max. average on-state current @ Max. T _C =	70*	Α	180° half sine wave conduction	
		62*	°C		
ITSM ,	Max. peak one cycle, non-repetitive surge current	955	A	50 Hz half cycle sine wave 6r 6 ms rectangular pulse with rated V_{RRM} applied following surge.	
		1000*	7 ^	60 Hz half cycle sine wave SCR turned fully on. or 5 ms rectangular pulse	
		1150		50 Hz haif cycle sine wave or 6 ms rectangular pulse Same conditions as above except with	
		1200 A	60 Hz half cycle sine wave or 5 ms rectangular pulse O Hz half cycle sine wave or 5 ms rectangular pulse		
l²t	Max, I ² t capability, for fusing	4550	A ² s	t = 10 ms Rated V _{RRM} applied	
		4150		t = 8.3 ms following surge, initial T _J = 125° C	
l ² t	Max. I ² t capability, for individual device fusing	6450	A ² s	t = 10 ms V _{RRM} = 0 following surge, initial T ₁ = 125° C	
		5900		1 t = 8.3 ms	
1 ² √t	Max. 12√t capability, for individual device fusing	64 500	A ² √s	t = 0.1 to 10ms.	
V _{TM}	Max. peak on-state voltage	1.85*	V	T _J = 25°C, I _{T(AV)} = 70A (220A peak)	
IH.	Max. holding current	500	mA	$T_C = 25^{\circ}$ C, anode supply = 22V, Initial $I_T = 3$ A.	
п	BLOCKING				
dv/dt	Min. critical rate of rise of off-state voltage	20*	V/ us	T _J = 125°C. Exponential to 100% rated V _{DRM} ; gate open circuited	
I _{RM} &	Max. peak reverse and off-state current 300V – 600V	5*	mA	Max. rated T _J , rated V _{RRM} , gate open circuited.	

¹ Meets MIL-S-19500/280A when ordered as JAN2N ----

 $[{]f 2}$ Units may be broken over without damage if di/dt does not exceed 20 A/ μ s.

³ I^2t for time $t_X = I^2\sqrt{t} \sqrt{t_X}$.

JEDEC registered values.

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2N3091 Series T- 25-17

ELECTRICAL SPECIFICATIONS (Continued)

		2N3901-98	Units	Conditions
	SWITCHING			
t _d	Typical delay time	1	1	T _C = 25°C, rated V _{DRM}
tr	Typical rise time	1	μs	I_{TM} = 50A resistive circuit, Gate pulse: 10V, 25Ω , $t_p = 6 \mu s$
t _q	Typical turn-off time	50	μs	T_C = 125° C, I_{TM} = 50A, di/dt = 5A/ μ s, V_R = 50V, reapplied dv/dt = 20V/ μ s linear to rated V_{DRM} , Gate bias: 0V, 100 Ω .
di/dt	Max. non-repetitive rate of rise of turned-on current = VRRM = 500V to 600V	300	A/μs	$T_C = 125^{\circ}C$, V_{VDM} = rated V_{DRM} . $I_{TM} = (2 \times di/dt)$ or $(2 \times rated T_{(AV)}A$ (whichever is the greater), Gate pulse: $20V$, 15Ω , $t_p = 6$ ms $t_p = 0.1 \mu$ s. Per JEDEC standard RS397, 5.2.2.6.
	= 700V to 1000V	225		
	= 1100V to 1400V	· 150		
	TRIGGERING			
P _{GM}	Max. peak gate power	5*	W	t _p ≤ 5 ms max.
P _G (AV)	Max. average gate power	0.5*	W	
+I _{GM}	Max. peak positive gate current	2	A	
+V _{GM}	Max. peak positive gate voltage	20*	V	
-V _{GM}	Max. peak negative gate voltage	5*	٧	
I _{GT}	Max. required DC gate current to trigger	200*	mA	T _C = -40°C. Max. required gate trigger voltage is the lowest value which will trigger all units with +6V anode-to-cathode.
		110	mA	T _C = 25°C
	_	50	mA	T _C = 125°C
	Typical DC gate current to trigger	25	mA	T _C = 25°C +6V anode-to-cathode
V _{GT}	Max. required DC gate voltage to trigger	3*	V	$T_C = -40^{\circ}$ C. Max. required gate trigger voltage is the lowest value which will trigger all units with +6V anode-to-cathode.
	•	2.5	V	T _C = 25°C
	Typical DC gate voltage to trigger	1	V	Tc = 25°C +6V anode-to-cathode
V _{GD}	Max. DC gate voltage not to trigger	0.20*	v	T_C = 125°C. Max. gate voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode-to-cathode

THERMAL-MECHANICAL SPECIFICATIONS

			2N3901-98	Units	Conditions
Tj	Operating junction temperature range		-40° to 125°	°C	
T _{stg}	Storage temperature range		-40* to 125*	°C	
R _{th} JC	Max. internal thermal resistance,		0.4*	K/W	DC operation
R _{thCS}	Thermal resistance, case to sink		0.1	K/W	Mounting surface smooth, flat and greased.
Т	Mounting torque	Min.	14.5 (125)	Nm	Non-lubricated threads
		Max.	17.0 (150)	(lbf-in)	
	Max, torque on screw in flag terminal		1.4 (12)	N m (lbf-in)	Non-lubricated threads. TO-208AD case only.
wt	Approximate weight	-	100 (3.5)	g (oz)	
Cese Style		TO-209AC (TO-94) (IR case Style A-11)		JEDEC .	

^{*}JEDEC registered values.

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2N3091 Series

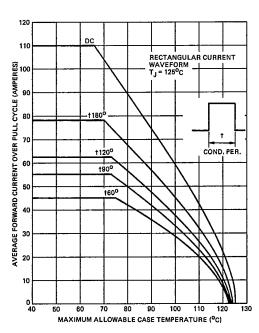


Fig. 1 — Average On-State Current Vs. Maximum Allowable Case Temperature (Sinusoidal Current Waveform, 50 to 400 Hz)

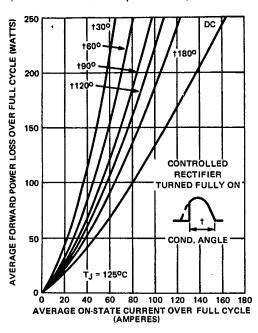


Fig. 3 — Maximum Low Level On-State Power Loss Vs. On-State Current (Sinusoidal Current Waveform)

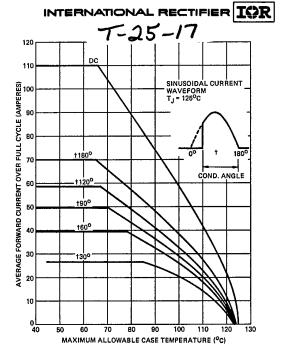


Fig. 2 — Average On-State Current Vs. Maximum Allowable Case Temperature (Rectangular - Current Waveform, 50 to 400 Hz)

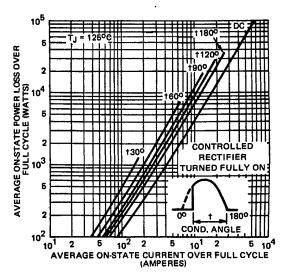


Fig. 4 — Maximum High Level On-State Power Loss Vs. On-State Current (Sinusoidal Current Waveform)

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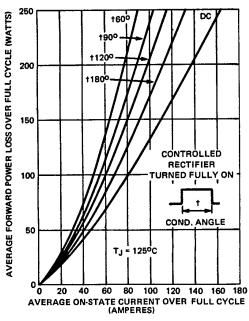


Fig. 5 — Maximum Low Level On-State Power Loss Vs. On-State Current (Rectangular Current Waveform)

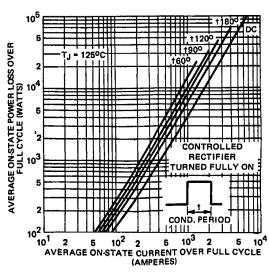


Fig. 6 — Maximum High Level On-State Power Loss Vs. On-State Current (Rectangular Current Waveform)

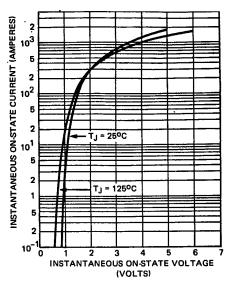


Fig. 7 — Maximum Instantaneous On-State Voltage Vs. Instantaneous On-State Current

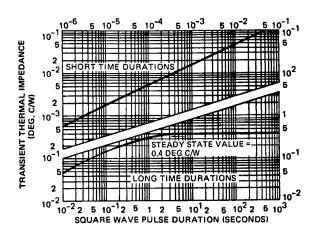


Fig. 8 — Maximum Transient Thermal Impedance, Junction to Case Vs. Pulse Duration

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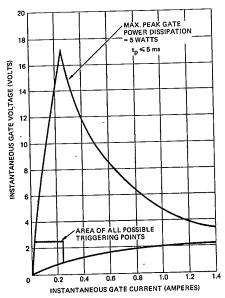


Fig. 9 — Gate Characteristics

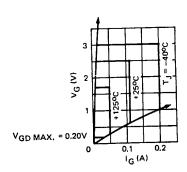


Fig. 9a — Area of All Possible Triggering Points

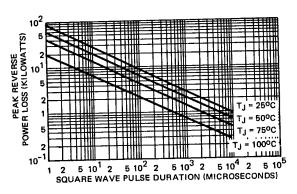


Fig. 10 — Maximum Allowable Reverse Power Dissipation Vs. Pulse Duration

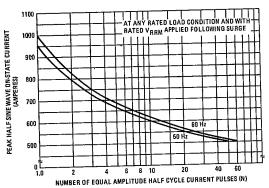


Fig. 11 — Maximum Non-Repetitive Surge Current Vs. Number of Current Pulses